

Silicon NPN Power Transistors

2SD1910

DESCRIPTION

www.datasheet4u.com

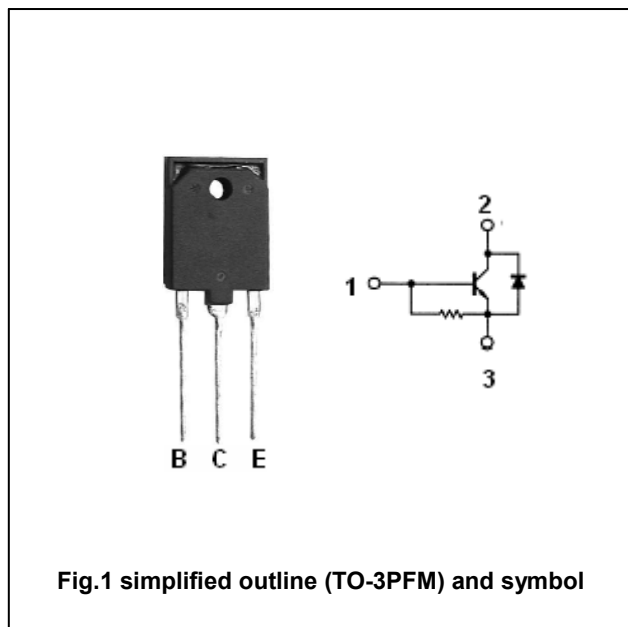
- With TO-3PFM package
- High breakdown voltage
- High speed switching
- Built-in damper diode

APPLICATIONS

- For use in TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		3	A
I_{CM}	Collector current-peak		6	A
P_C	Collector power dissipation	$T_C = 25\square$	40	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

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 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C = 0.1\text{A}$; $I_B = 0$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 2.5\text{A}$; $I_B = 0.8\text{A}$			5.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = 2.5\text{A}$; $I_B = 0.8\text{A}$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = 800\text{V}$; $I_E = 0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB} = 6\text{V}$; $I_C = 0$	50		200	mA
h_{FE}	DC current gain	$I_C = 0.5\text{A}$; $V_{CE} = 5\text{V}$	8		25	
V_F	Diode forward voltage	$I_F = 3\text{A}$			2.0	V

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PACKAGE OUTLINE

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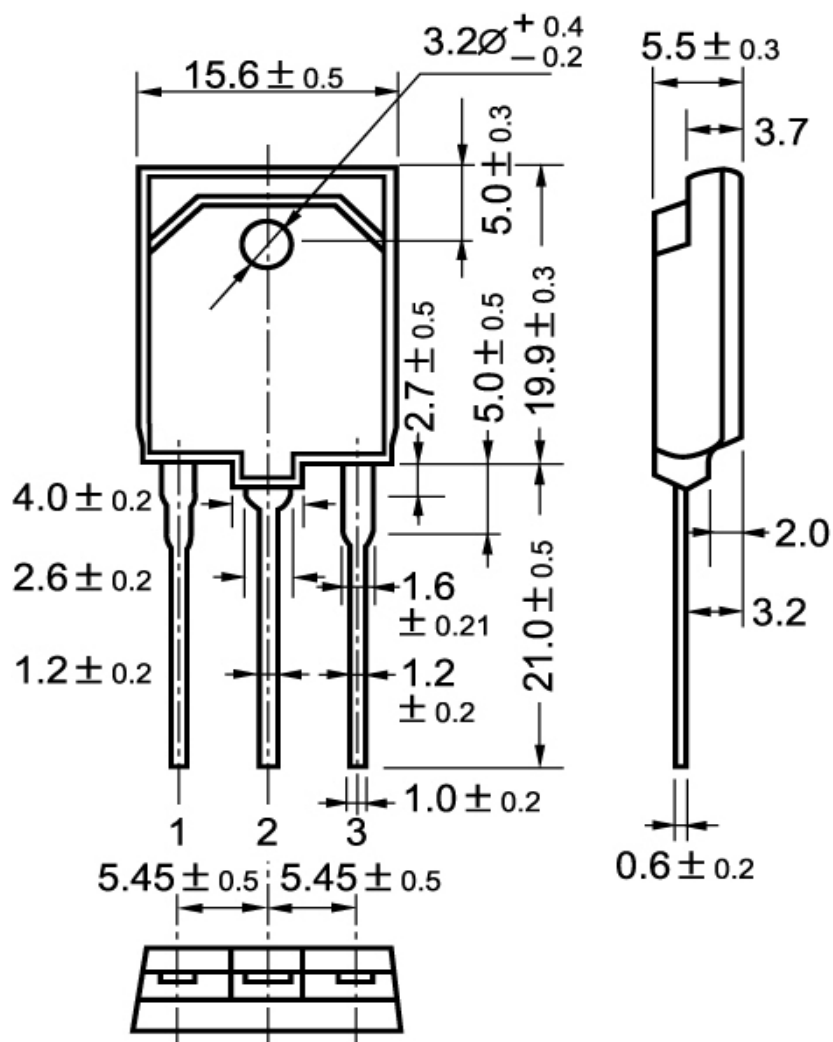


Fig.2 outline dimensions